TYN30H-800C 30A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, TYN30H-800C of silicon controlled rectifiers provides high dV/dt rate with strong resistance to electromagnetic interference.
It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. Package TO-220C is RoHS compliant.

MAIN FEATURES

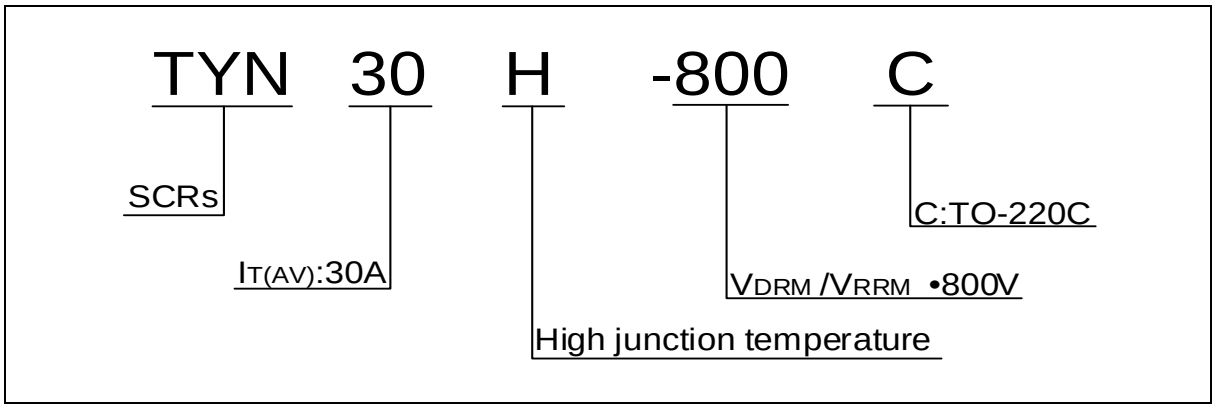
Symbol	Value	Unit
$I_{T(AV)}$	30	A

10 (m533.4 70.31 22.68 re f 325.28 533.4 0.418

Peak gate current (t_p=20 s , T_j=150)	I_{GM}	10	A
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25)

ORDERING INFORMATION



MARKING

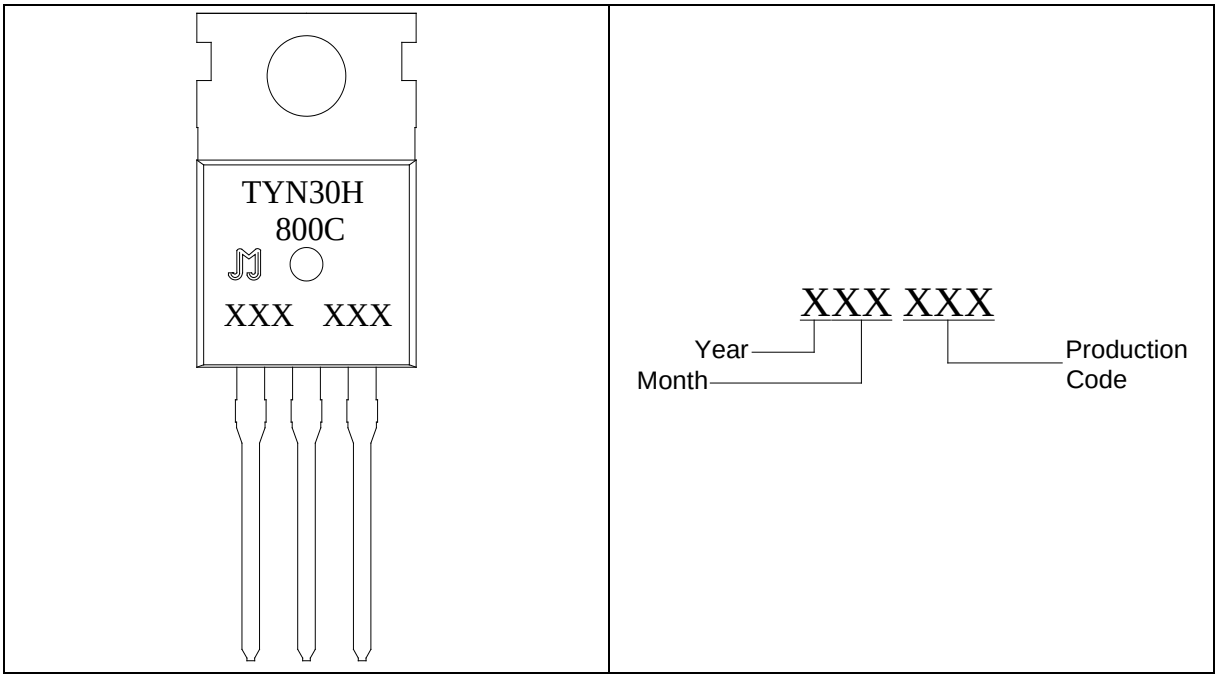


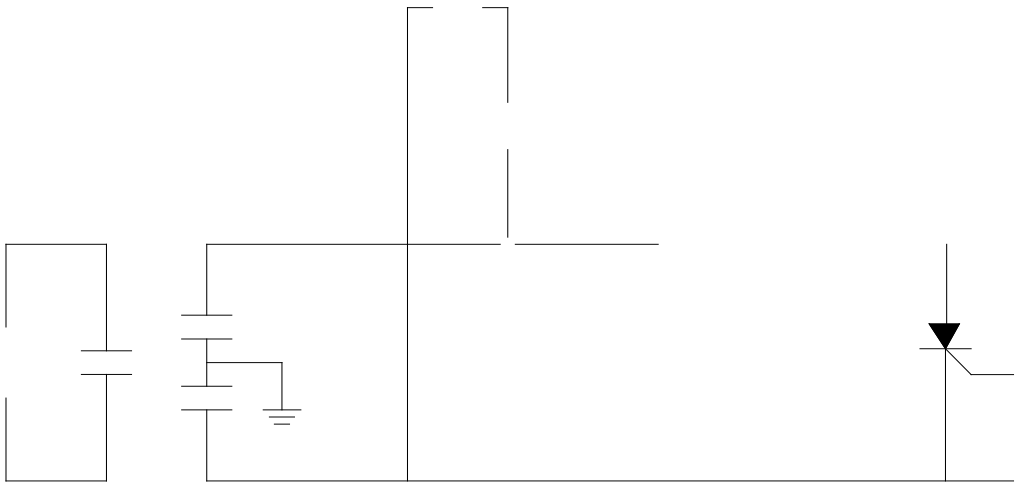
FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature





FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards.



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